

## REMARKS

In the Advisory Action, the Examiner maintained his rejection of Claims 1-7 under 35 U.S.C. §112 first paragraph, as not being in compliance with the written description requirement; Claims 4 and 7 under 35 U.S.C. §112 second paragraph, as being indefinite; Claims 1-3 and 6 under 35 U.S.C. §102(b) as being anticipated by U.S. Patent No. 4,851,078 (Short); and Claim 5 under 35 U.S.C. §103(a) as being unpatentable over Short in view of U.S. Patent No. 5,506,433 (Ohori).

In response to the Advisory Action, Claims 1-4 have been amended to more clearly point out that a hybrid substrate of the present invention includes a substrate having a plurality of pockets patterned thereon; and **at least two different single crystal conductive materials** deposited within each pocket **for fabricating a plurality of devices**. Furthermore, a new Claim 19 has been added to replace Claim 7. Claim 19 recites that each inventive pocket has a greater surface area than a surface area of a cross-section of the **at least two different single crystal conductive materials** deposited within that pocket.

The object of the present invention is to build a plurality of different devices using different substrates on one chip by using a plurality of single crystal conductive materials deposited within pockets formed on the hybrid substrate. The plurality of different devices are built or fabricated within each of the different single crystal conductive materials. Please refer to Figures 4 and 6 of the present application, where different materials are depicted by materials 150A, 150B, and 150C.

The finished structure of Short, shown in FIG. 20, has a typical dielectric isolation (DI) structure with single crystal silicon islands 70, surrounded by a sidewall oxide 60 and bottom oxide 45, 55, separated by polycrystalline silicon 65 formed into the surface. It is not possible for Short to have different single crystal conductive materials in islands 70 of FIG. 20 or different sections of the substrate 10 of FIG. 10.

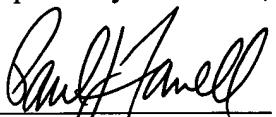
The material used inside the pocket in Short is of the same kind as the substrate. As shown in FIGs. 2-12 and 14-20 of Short, the material used inside all the pockets of Short is formed by the uniform epitaxial layer 15. This contradicts and teaches away from the present

invention, where different single crystal conductive materials are placed in each pocket. Because different single crystal conductive materials are used, the thickness of each of these materials in the separate pockets is different before planarization as indicated in Fig. 4, t1, t2 and t3, etc. Contrarily, anything formed inside the trench (moat) of Short cannot be used to form conductive devices, since Short teaches materials used for isolation and filling purposes. Short does not teach or describe "at least two different single crystal conductive materials deposited within each pocket of the plurality of pockets for fabricating a plurality of devices" recited in Claim 1 as amended.

In light of the discussion above, it is respectfully submitted that independent Claim 1 overcomes the stated rejections. Without conceding the patentability per se of dependent Claims 2-6 and new Claim 19, it is respectfully submitted that these claims also overcome the rejections by virtue of their dependence on Claim 1.

Applicants submit that Claims 1-6 and new Claim 19 are believed to be in condition for allowance. Allowance is respectfully requested. Should the Examiner believe that a telephone conference or personal interview would facilitate resolution of any remaining matters, the Examiner may contact Applicants' attorney at the number given below:

Respectfully submitted,

  
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